New Jersey Semi-Conductor Products, Inc.

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NPN POWER TRANSISTORS

COMPLEMENTARY TO THE D41E SERIES

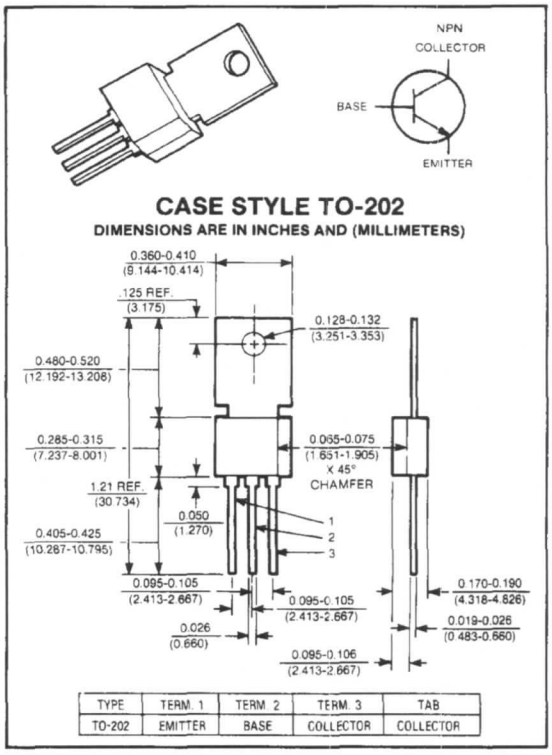
D40E Series

30 - 80 VOLTS
2 AMP, 8 WATTS

D40E series are power transistors designed for various specific and general purpose applications, such as: output and driver stages of amplifiers operating at frequencies from DC to greater than 0.1MHz; series, shunt and switching regulators; low and high frequency inverters/converters; and many others.

Features:

- High free-air power dissipation
- NPN complement to D41E PNP
- Low collector saturation voltage (0.5V typ. @ 1.0A I_C)
- Excellent linearity
- Fast switching



TYPE	TERM. 1	TERM. 2	TERM. 3	TAB
TO-202	EMITTER	BASE	COLLECTOR	COLLECTOR

maximum ratings (T_A = 25° C) (unless otherwise specified)

RATING	SYMBOL	D40E1	D40E5	D40E7	UNITS
Collector-Emitter Voltage	V_{CEO}	30	60	80	Volts
Collector-Emitter Voltage	V_{CES}	45	70	90	Volts
Emitter Base Voltage	V_{EBO}	5	5	5	Volts
Collector Current — Continuous Peak(1)	I_C I_{CM}	2 3	2 3	2 3	A
Base Current — Continuous	I_B	1	1	1	A
Total Power Dissipation @ T_A = 25°C @ T_C = 25°C	P_D	1.33 8	1.33 8	1.33 8	Watts
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	-55 to +150	-55 to +150	°C

thermal characteristics

Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	75	75	75	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	15.6	15.6	15.6	°C/W
Maximum Lead Temperature for Soldering Purposes: ⅛" from Case for 5 Seconds	T_L	+260	+260	+260	°C

(1) Pulse Test Pulse Width = 300ms Duty Cycle ≤ 2%.

electrical characteristics (T_C = 25° C) (unless otherwise specified)

CHARACTERISTIC		SYMBOL	MIN	TYP	MAX	UNIT
off characteristics[1]						
Collector-Emitter Sustaining Voltage (I_C = 10mA)	D40E1	$V_{CEO(sus)}$	30	—	—	Volts
	D40E5		60	—	—	
	D40E7		80	—	—	
Collector Cutoff Current (V_{CE} = Rated V_{CES})		I_{CES}	—	—	0.1	μA
Emitter Cutoff Current (V_{EB} = 5V)		I_{EBO}	—	—	0.1	μA
second breakdown						
Second Breakdown with Base Forward Biased		FBSOA	SEE FIGURE 1			
on characteristics						
DC Current Gain (I_C = 100mA, V_{CE} = 2V)		h_{FE}	50	—	—	—
(I_C = 1A, V_{CE} = 2V)		h_{FE}	10	—	—	—
Collector-Emitter Saturation Voltage (I_C = 1.0A, I_B = 0.1A)		$V_{CE(sat)}$	—	—	1.0	Volts
Base-Emitter Saturation Voltage (I_C = 1.0mA, I_B = 0.1A)		$V_{BE(sat)}$	—	—	1.3	Volts
dynamic characteristics						
Collector Capacitance (V_{CB} = 10V, f = 1M_{Hz})		C_{CBO}	—	9	—	pF
Current-Gain — Bandwidth Product (I_C = 100mA, V_{CE} = 10V)		f_T	—	230	—	MHz
switching characteristics						
Resistive Load						
Delay Time + Rise Time	I_C = 1A, I_{B1} = I_{B2} = 0.1A	$t_d + t_r$	—	130	—	nS
Storage Time	V_{CC} = 30V, t_p = 25 μsec	t_s	—	400	—	
Fall Time		t_f	—	170	—	

(1) Pulse Test PW = 300ms Duty Cycle ≤ 2%.

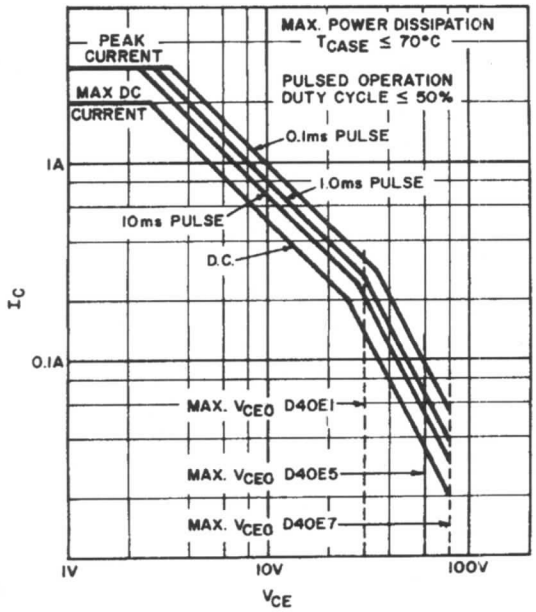


FIG. 1 SAFE REGION OF OPERATION

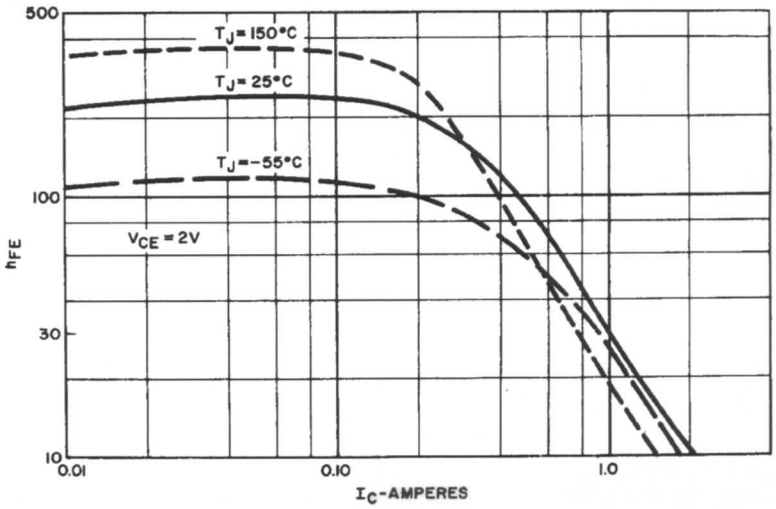


FIG. 2 TYPICAL H_{FE} VS I_C